# MSKSEMI 美森科















PIFD

## **MMST2222A**

**Product specification** 





#### **FEATURES**

- Epitaxial planar die construction
- Complementary PNP Type available(MMST2907A)

#### **Reference News**

PACKAGE	MARKING	
3	1. BASE	
2	2. EMITTER	K3P
	3. COLLECTOR	
1		
SOT-	323	

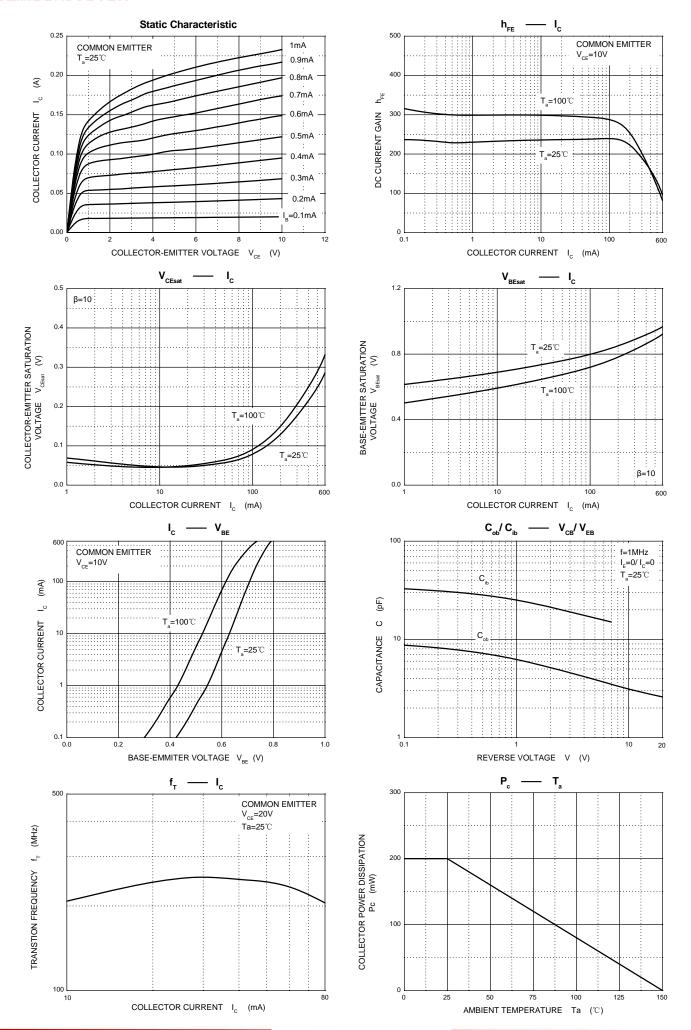
## MAXIMUM RATINGS (Ta=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage	75	V
Vceo	Collector-Emitter Voltage	40	V
V <sub>EBO</sub>	Emitter-Base Voltage	6	V
Ic	Collector Current -Continuous	600	mA
Pc	Collector Dissipation	200	mW
T <sub>J</sub> ,T <sub>stg</sub>	Operation Junction and Storage Temperature Range	-55~+150	℃

### **ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)**

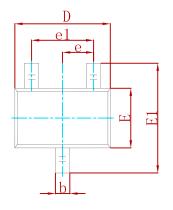
Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = 10μA, I <sub>E</sub> =0	75			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	Ic= 10mA, I <sub>B</sub> =0	40			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =10μA, I <sub>C</sub> =0	6			V
Collector cut-off current	Ісво	$V_{CB}$ =70 V, $I_{E}$ =0			100	nA
Collector cut-off current	ICEO	V <sub>CE</sub> =35V , I <sub>B</sub> =0			100	nA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = 3V , I <sub>C</sub> =0			100	nA
DC current gain	h <sub>FE(1)</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =0.1mA	35			
	h <sub>FE(2)</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> = 1mA	50			
	h <sub>FE(3)</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> = 10mA	75			
	h <sub>FE(4)</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> = 150mA	100		300	
	h <sub>FE(5)</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> = 500mA	40			
	h <sub>FE(6)</sub>	V <sub>CE</sub> =1V, I <sub>C</sub> = 150mA	35			
Collector-emitter saturation voltage	V <sub>CE</sub> (sat)	l <sub>C</sub> =500 mA, I <sub>B</sub> = 50mA I <sub>C</sub> =150 mA, I <sub>B</sub> =15mA			1 0.3	V
Base-emitter saturation voltage	V <sub>BE</sub> (sat)	l <sub>C</sub> =500 mA, I <sub>B</sub> = 50mA l <sub>C</sub> =150 mA, I <sub>B</sub> =15mA			2.0 1.2	V
Transition frequency	f⊤	V <sub>CE</sub> =20V, I <sub>C</sub> = 20mA f=100MHz	300			MHz
Output Capacitance	Cob	V <sub>CB</sub> =10V, I <sub>E</sub> = 0,f=1MHz			8	pF
Delay time	t <sub>d</sub>	V <sub>CC</sub> =30V, V <sub>BE(off)</sub> =-0.5V			10	ns
Rise time	tr	I <sub>C</sub> =150mA , I <sub>B1</sub> = 15mA			25	ns
Storage time	ts	V <sub>CC</sub> =30V, I <sub>C</sub> =150mA			225	ns
Fall time	t <sub>f</sub>	I <sub>B1</sub> =-I <sub>B2</sub> =15mA			60	ns

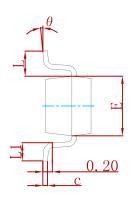


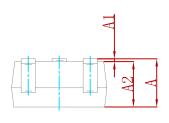




#### **PACKAGEMECHANICALDATA**

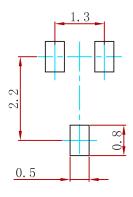






Symbol	Dimensions	In Millimeters	Dimensions In Inches		
Syllibol	Min	Max	Min	Max	
А	0.900	1.100	0.035	0.043	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.000	0.035	0.039	
b	0.200	0.400	0.008	0.016	
С	0.080	0.150	0.003	0.006	
D	2.000	2.200	0.079	0.087	
Е	1.150	1.350	0.045	0.053	
E1	2.150	2.450	0.085	0.096	
е	0.650 TYP		0.026 TYP		
e1	1.200	1.400	0.047	0.055	
L	0.525 REF		0.021 REF		
L1	0.260	0.460	0.010	0.018	
θ	0°	8°	0°	8°	

## **Suggested Pad Layout**



#### Note:

- 1. Controlling dimension:in millimeters.
- 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.

### **REEL SPECIFICATION**

P/N	PKG	QTY	
MMST2222A	SOT-323	3000	



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